

# Field Stop Trench IGBT

**50 A, 650 V**

## FGHL50T65LQDTL4

Field stop 4<sup>th</sup> generation Low  $V_{CE(Sat)}$  IGBT technology and Full current rated copack Diode technology.

### Features

- Maximum Junction Temperature:  $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(Sat)} = 1.15\text{ V (Typ.) @ } I_C = 50\text{ A}$
- 100% of the Parts are Tested for  $I_{LM}$  (Note 2)
- Smooth and Optimized Switching
- Tight Parameter Distribution
- Co-packed with Soft and Fast Recovery Diode
- These Devices are Pb-Free and are RoHS Compliant

### Typical Applications

- Solar Inverter
- UPS, ESS
- PFC, Converters

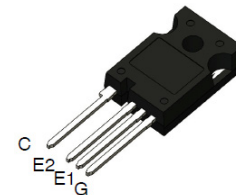
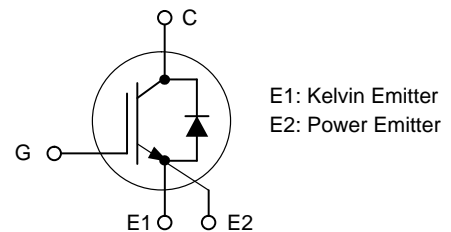
### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector to Emitter Voltage	$V_{CES}$	650	V
Gate to Emitter Voltage Transient Gate to Emitter Voltage	$V_{GES}$	$\pm 20$ $\pm 30$	V
Collector Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_C$	80 50	A
Pulsed Collector Current (Note 2)	$I_{LM}$	200	A
Pulsed Collector Current (Note 3)	$I_{CM}$	200	A
Diode Forward Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_F$	60 50	A
Pulsed Diode Maximum Forward Current	$I_{FM}$	200	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$P_D$	341 170	W
Operating Junction and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to +175	$^\circ\text{C}$
Maximum Lead Temp. for Soldering Purposes (1/8" from case for 5 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

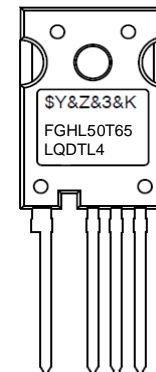
1. Value limit by bond wire
2.  $V_{CC} = 400\text{ V}$ ,  $V_{GE} = 15\text{ V}$ ,  $I_C = 200\text{ A}$ , Inductive Load, 100% tested
3. Repetitive rating: pulse width limited by max. junction temperature

**50 A, 650 V**  
 **$V_{CE(Sat)} = 1.15\text{ V}$**



TO-247-4LD  
CASE 340CJ

### MARKING DIAGRAM



&Y = onsemi Logo  
&Z = Assembly Plant Code  
&3 = 3-Digit Date Code  
&K = 2-Digit Lot Traceability Code  
FGHL50T65LQDTL4 = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping
FGHL50T65LQDTL4	TO-247-4LD	450 Units/Tube

# FGHL50T65LQDTL4

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.44	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.74	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector to Emitter breakdown voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$BV_{CES}$	650	–	–	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$	–	0.6	–	V/°C
Collector to Emitter cut-off current	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	$I_{CES}$	–	–	250	μA
Gate leakage current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	–	–	±400	nA

### ON CHARACTERISTICS

Gate to Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 50\text{ mA}$	$V_{GE(th)}$	3.0	4.5	6.0	V
Collector to Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 25^\circ\text{C}$ $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$	–	1.15 1.22	1.35 –	V

### DYNAMIC CHARACTERISTICS

Input capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	–	10615	–	pF
Output capacitance		$C_{oes}$	–	120	–	
Reverse transfer capacitance		$C_{res}$	–	50	–	
Gate charge total	$V_{CE} = 400\text{ V}, I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$	–	509	–	nC
Gate-to-emitter charge		$Q_{ge}$	–	52	–	
Gate-to-collector charge		$Q_{gc}$	–	167	–	

### SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^\circ\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 25\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	28	–	ns	
Rise time		$t_r$	–	12	–		
Turn-off delay time		$t_{d(off)}$	–	424	–		
Fall time			$t_f$	–	140	–	mJ
Turn-on switching loss		$E_{on}$	–	0.41	–		
Turn-off switching loss		$E_{off}$	–	0.86	–		
Total switching loss		$E_{ts}$	–	1.26	–		
Turn-on delay time	$T_J = 25^\circ\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 50\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	30	–	ns	
Rise time		$t_r$	–	24	–		
Turn-off delay time		$t_{d(off)}$	–	412	–		
Fall time			$t_f$	–	116	–	mJ
Turn-on switching loss		$E_{on}$	–	0.72	–		
Turn-off switching loss		$E_{off}$	–	1.54	–		
Total switching loss		$E_{ts}$	–	2.26	–		

# FGHL50T65LQDTL4

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on delay time	$T_J = 175^\circ\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 25\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	26	–	ns
Rise time		$t_r$	–	16	–	
Turn-off delay time		$t_{d(off)}$	–	484	–	
Fall time		$t_f$	–	220	–	
Turn-on switching loss		$E_{on}$	–	0.81	–	mJ
Turn-off switching loss		$E_{off}$	–	1.19	–	
Total switching loss		$E_{ts}$	–	2	–	
Turn-on delay time		$T_J = 175^\circ\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 50\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	28	–
Rise time	$t_r$		–	28	–	
Turn-off delay time	$t_{d(off)}$		–	476	–	
Fall time	$t_f$		–	176	–	
Turn-on switching loss	$E_{on}$		–	1.48	–	mJ
Turn-off switching loss	$E_{off}$		–	2.24	–	
Total switching loss	$E_{ts}$		–	3.72	–	

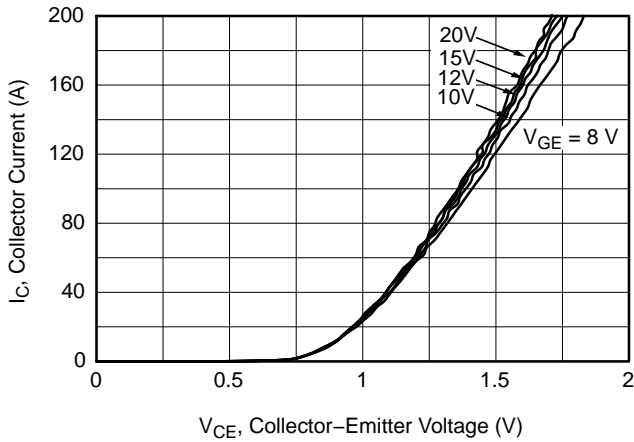
### DIODE CHARACTERISTICS

Diode Forward Voltage	$I_F = 50\text{ A}, T_J = 25^\circ\text{C}$	$V_{FM}$	–	1.65	2.1	V
	$I_F = 50\text{ A}, T_J = 175^\circ\text{C}$		–	1.55	–	
Reverse Recovery Energy	$T_J = 25^\circ\text{C},$ $V_R = 400\text{ V},$ $I_F = 25\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	–	77	–	$\mu\text{J}$
Reverse Recovery Time		$T_{rr}$	–	57	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	532	–	nC
Reverse Recovery Current		$I_{rr}$	–	19	–	A
Reverse Recovery Energy	$T_J = 25^\circ\text{C},$ $V_R = 400\text{ V},$ $I_F = 50\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	–	127	–	$\mu\text{J}$
Reverse Recovery Time		$T_{rr}$	–	75	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	783	–	nC
Reverse Recovery Current		$I_{rr}$	–	21	–	A
Reverse Recovery Energy	$T_J = 175^\circ\text{C},$ $V_R = 400\text{ V},$ $I_F = 25\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	–	356	–	$\mu\text{J}$
Reverse Recovery Time		$T_{rr}$	–	101	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	1725	–	nC
Reverse Recovery Current		$I_{rr}$	–	35	–	A
Reverse Recovery Energy	$T_J = 175^\circ\text{C},$ $V_R = 400\text{ V},$ $I_F = 50\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	–	549	–	$\mu\text{J}$
Reverse Recovery Time		$T_{rr}$	–	132	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	2465	–	nC
Reverse Recovery Current		$I_{rr}$	–	38	–	A

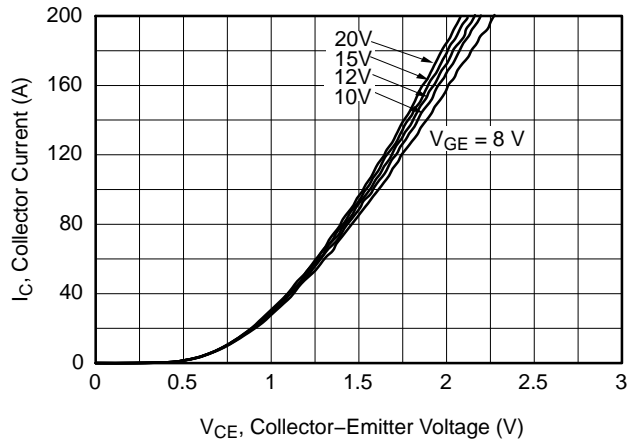
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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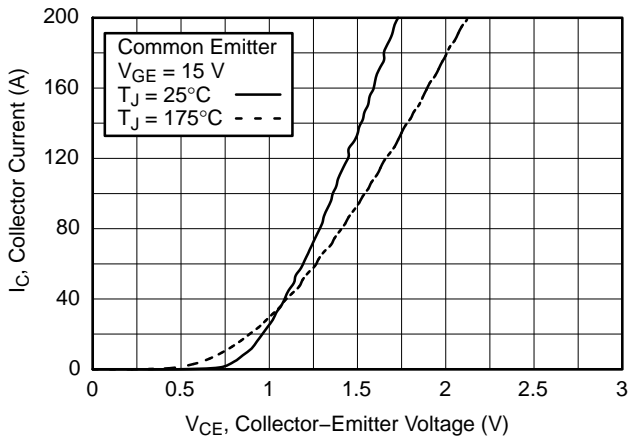
## TYPICAL CHARACTERISTICS



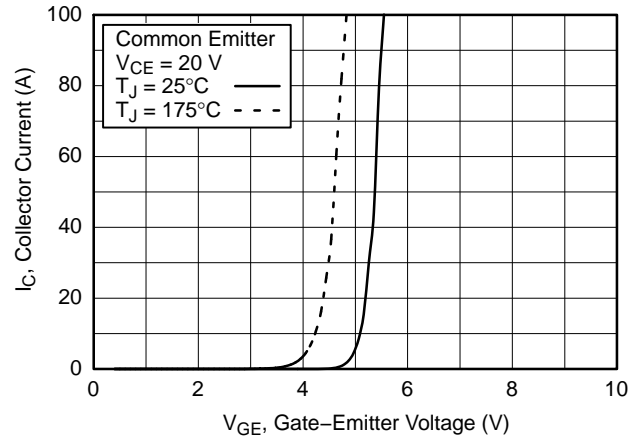
**Figure 1. Typical Output Characteristics**  
( $T_J = 25^\circ\text{C}$ )



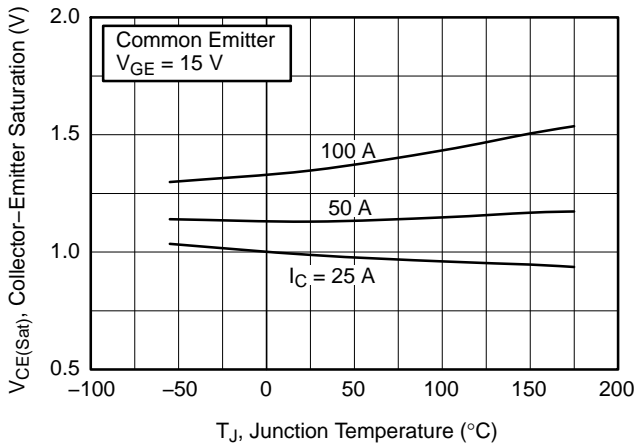
**Figure 2. Typical Output Characteristics**  
( $T_J = 175^\circ\text{C}$ )



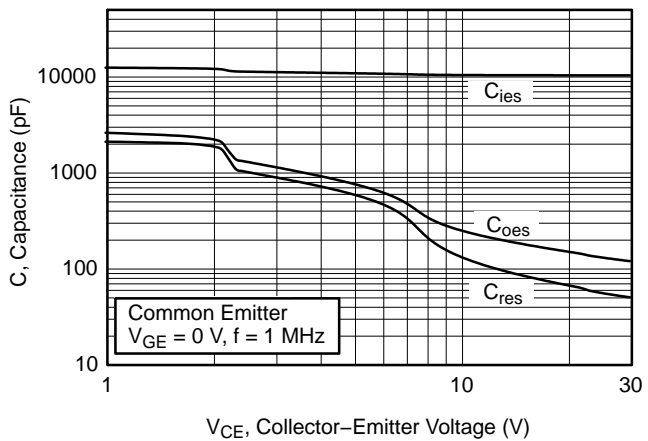
**Figure 3. Typical Saturation Voltage Characteristics**



**Figure 4. Typical Transfer Characteristics**



**Figure 5. Saturation Voltage vs. Junction Temperature**



**Figure 6. Capacitance Characteristics**

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## TYPICAL CHARACTERISTICS (continued)

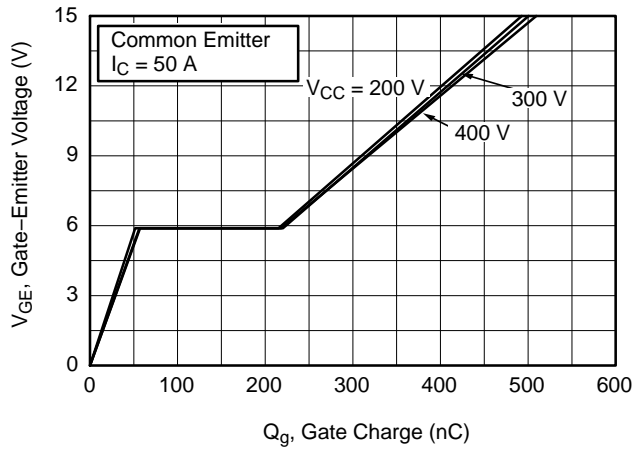


Figure 7. Gate Charge Characteristics

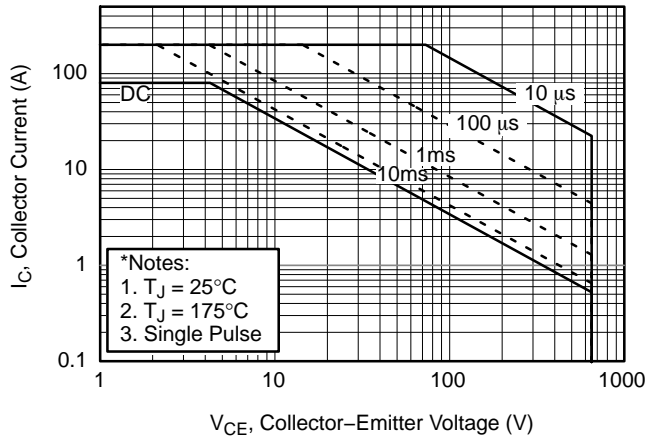


Figure 8. SOA Characteristics

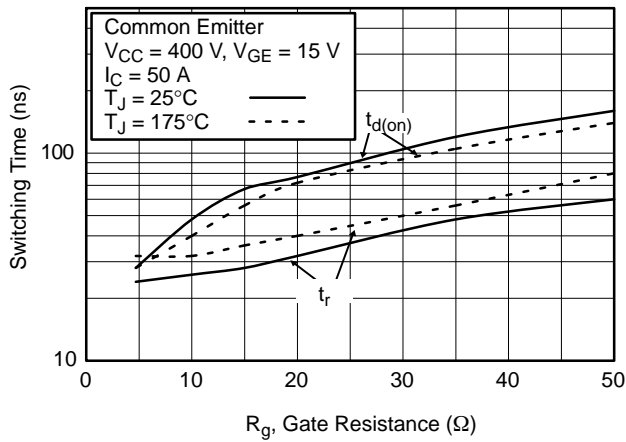


Figure 9. Turn-On Characteristics vs. Gate Resistance

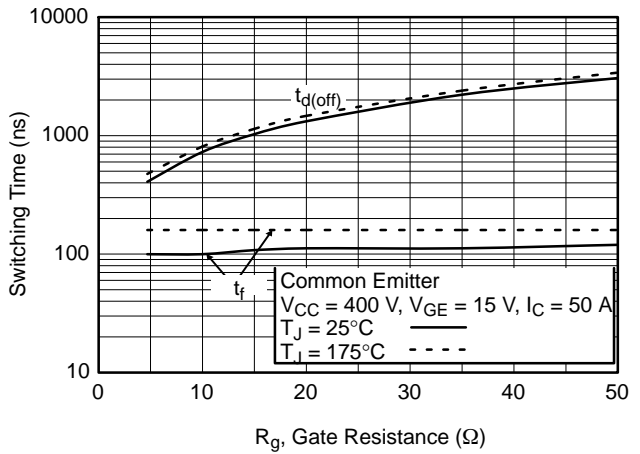


Figure 10. Turn-Off Characteristics vs. Gate Resistance

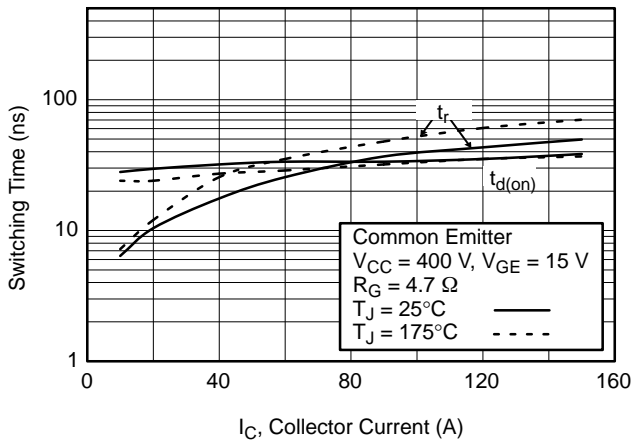


Figure 11. Turn-On Characteristics vs. Collector Current

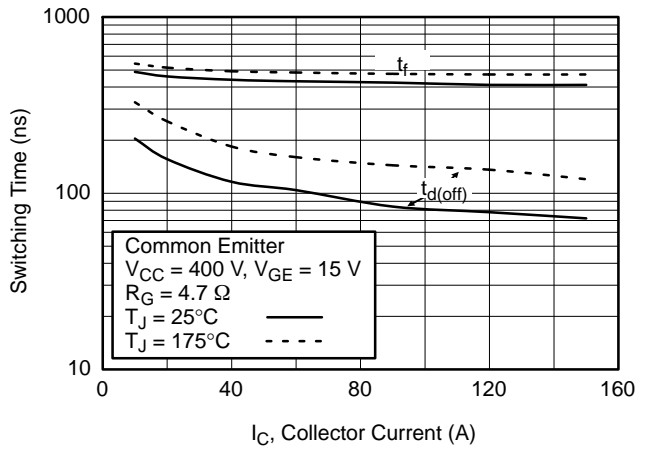


Figure 12. Turn-Off Characteristics vs. Collector Current

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## TYPICAL CHARACTERISTICS (continued)

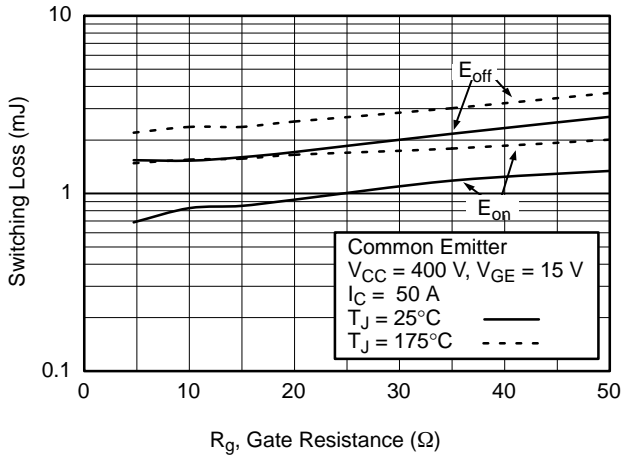


Figure 13. Switching Loss vs. Gate Resistance

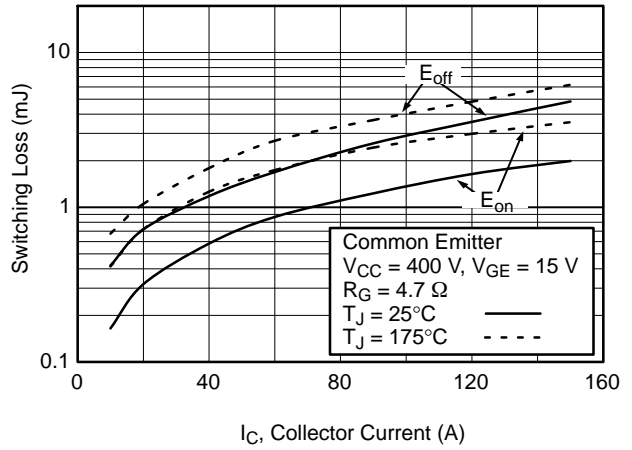


Figure 14. Switching Loss vs. Collector Current

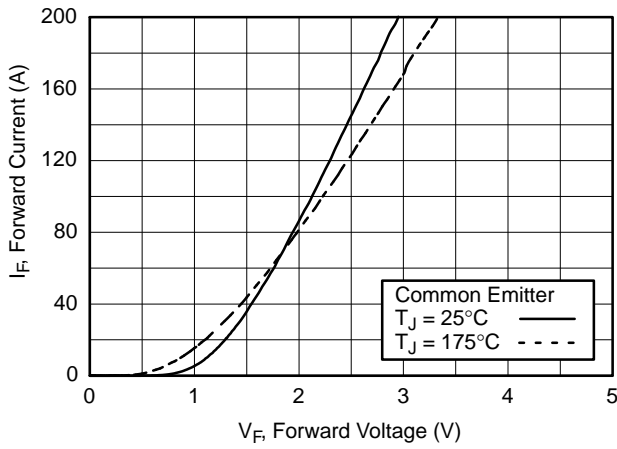


Figure 15. Forward Characteristics

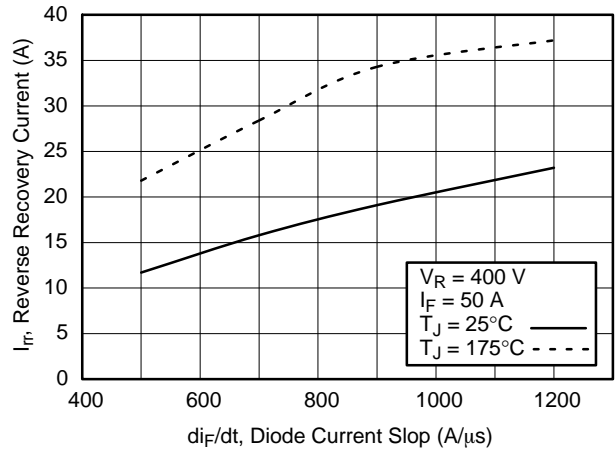


Figure 16. Reverse Recovery Current

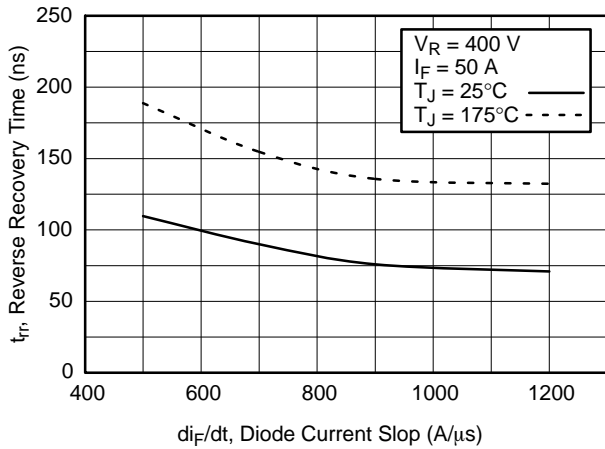


Figure 17. Reverse Recovery Time

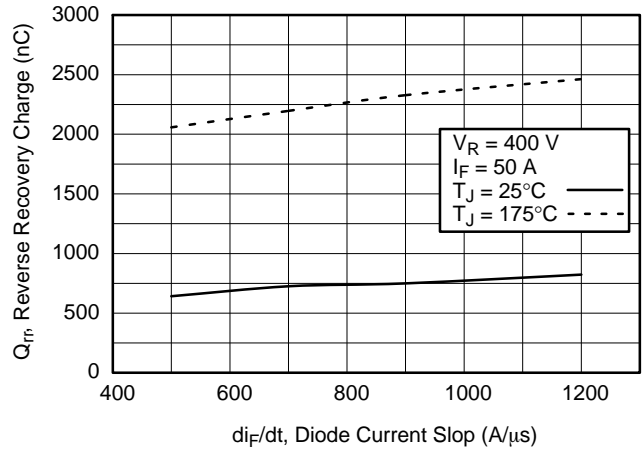


Figure 18. Stored Charge

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## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

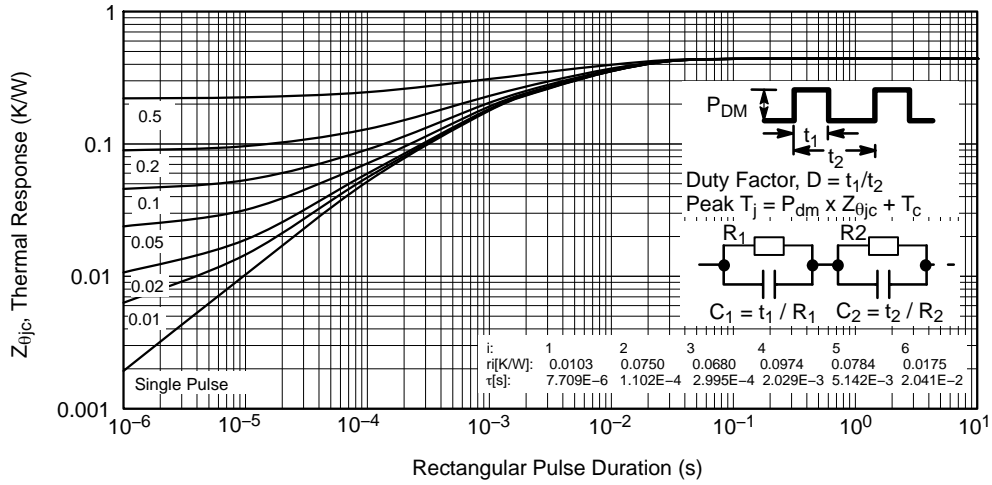


Figure 19. Transient Thermal Impedance of IGBT

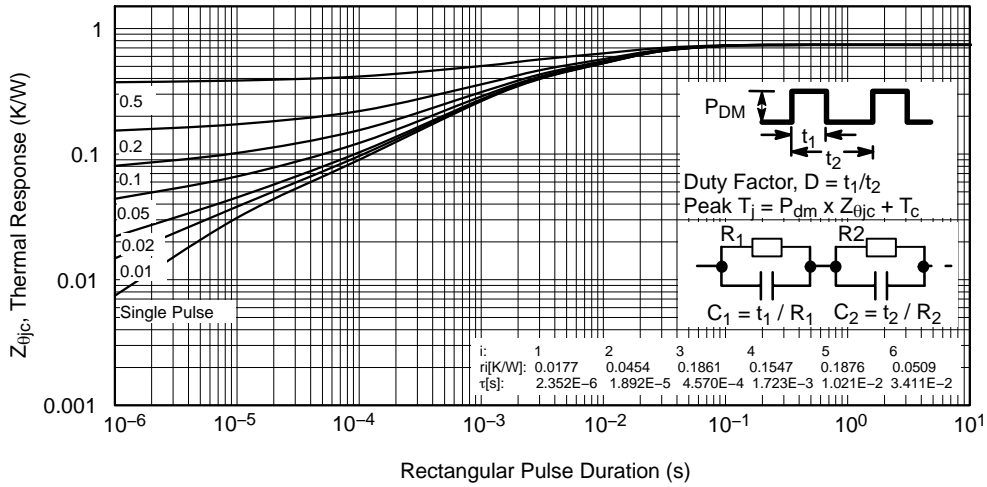
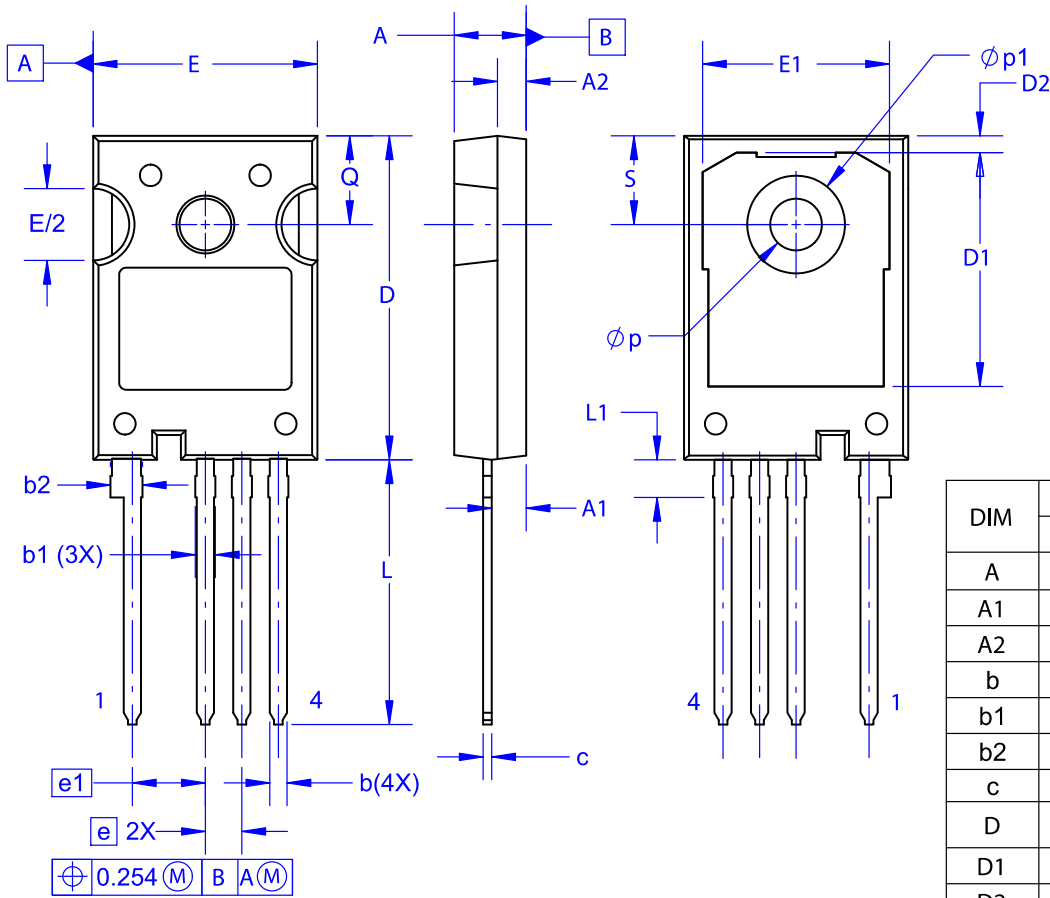


Figure 20. Transient Thermal Impedance of Diode

# FGHL50T65LQDTL4

## PACKAGE DIMENSIONS

TO-247-4LD  
CASE 340CJ  
ISSUE A



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

**NOTES:**

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.